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Phase Control Thyristor

DS5833-4 June 2014 (LN31648)

FEATURES

- Double Side Cooling
- High Surge Capability

KEY PARAMETERS

V _{DRM}	8500V
I _{T(AV)}	387A
I _{TSM}	5250A
dV/dt*	1500V/µs
dl/dt	200A/us

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages V _{DRM} and V _{RRM} V	Conditions
DCR390J85* DCR390J80 DCR390J70	8500 8000 7000	$ \begin{array}{l} T_{vj} = -40^{\circ}C \ to \ 125^{\circ}C, \\ I_{DRM} = I_{RRM} = 100 mA, \\ V_{DRM}, \ V_{RRM} \ t_p = 10 ms, \\ V_{DSM} \& \ V_{RSM} = \\ V_{DRM} \& \ V_{RRM} \ + 100 V \\ respectively \end{array} $

Lower voltage grades available. *8200V @ -40° C, 8500V @ 0° C

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR390J85

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

* Higher dV/dt selections available

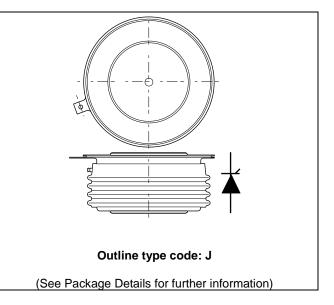
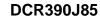


Fig. 1 Package outline





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CURRENT RATINGS

 $T_{case} = 60^{\circ}C$ unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Sid	de Cooled			
I _{T(AV)}	Mean on-state current	Half wave resistive load	387	А
I _{T(RMS)}	RMS value	-	608	А
Ι _Τ	Continuous (direct) on-state current	-	583	А

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine, $T_{case} = 125^{\circ}C$	5.25	kA
l ² t	I ² t for fusing	$V_R = 0$	0.138	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Condition	s	Min.	Max.	Units
R _{th(j-c)}	Thermal resistance – junction to case	Double side cooled	DC	-	0.0379	°C/W
		Single side cooled	Anode DC	-	0.0745	°C/W
			Cathode DC	-	0.0797	°C/W
R _{th(c-h)}	Thermal resistance – case to heatsink	Clamping force 11.5kN	Double side	-	0.0072	°C/W
		(with mounting compound)	Single side	-	.0144	°C/W
T _{vj}	Virtual junction temperature	Blocking V _{DRM} / _{VRRM}		-	125	°C
T _{stg}	Storage temperature range			-55	125	°C
Fm	Clamping force			10	13	kN



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DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditio	ons	Min.	Max.	Units
I _{RRM} /I _{DRM}	Peak reverse and off-state current	At V _{RRM} /V _{DRM} , T _{case} = 125°C		-	100	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V _{DRM} , T _j = 125°C, ga	ate open	-	1500	V/µs
dl/dt	Rate of rise of on-state current	From 67% V_{DRM} to 2x $I_{\text{T(AV)}}$	Repetitive 50Hz	-	100	A/µs
		Gate source 30V, 10Ω ,	Non-repetitive	-	200	A/µs
		t _r < 0.5µs, T _j = 125°C				
V _{T(TO)}	Threshold voltage – Low level	50A to 400A at $T_{case} = 125^{\circ}C$	2	-	1.162	V
	Threshold voltage – High level	400A to 1600A at $T_{case} = 125$	5°C	-	1.3063	V
r⊤	On-state slope resistance – Low level	50A to 400A at T _{case} = 125°C	2	-	3.153	mΩ
	On-state slope resistance – High level	400A to 1600A at $T_{case} = 125$	5°C	-	2.763	mΩ
t _{gd}	Delay time	$V_D = 67\% V_{DRM}$, gate source	30V, 10Ω	-	3	μs
		$t_r = 0.5 \mu s, T_j = 25^{\circ}C$				
t _q	Turn-off time	$T_j = 125^{\circ}C, V_R = 100V, dI/dt$	= 5A/µs,	-	1200	μs
		$dV_{DR}/dt = 20V/\mu s$ linear				
Qs	Stored charge	$I_T = 500A, T_j = 125^{\circ}C, dI/dt = 5A/\mu s,$		2000	3000	μC
۱L	Latching current	$T_j = 25^{\circ}C, V_D = 5V$		-	3	А
Ι _Η	Holding current	$T_j = 25^{\circ}C, R_{G-K} = \infty, I_{TM} = 50$	0A, I _T = 5A	-	300	mA



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GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V _{GT}	Gate trigger voltage	$V_{DRM} = 5V, T_{case} = 25^{\circ}C$	1.5	V
V_{GD}	Gate non-trigger voltage	At 50% V _{DRM} , T _{case} = 125°C	0.4	V
I _{GT}	Gate trigger current	$V_{DRM} = 5V, T_{case} = 25^{\circ}C$	350	mA
I _{GD}	Gate non-trigger current	At 50% V _{DRM} , T _{case} = 125°C	15	mA

CURVES

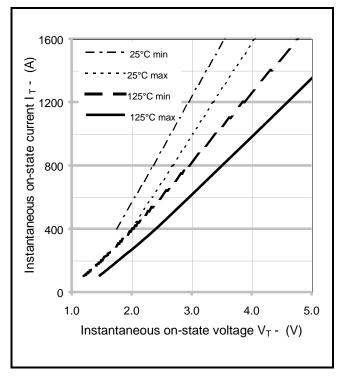


Fig.2 Maximum & minimum on-state characteristics

V_{TM} EQUATION

 $V_{TM} = A + Bln (I_T) + C.I_T + D.\sqrt{I_T}$

Where A = 1.545561B = -0.202735C = 0.001865D = 0.066158

these values are valid for T_j = 125°C for I_T 50A to 1600A



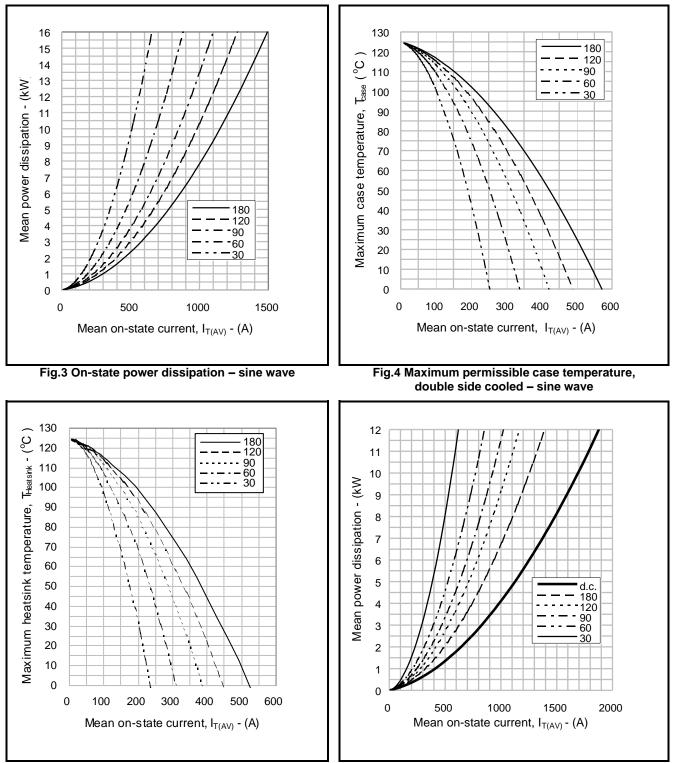


Fig.5 Maximum permissible heatsink temperature, double side cooled – sine wave

Fig.6 On-state power dissipation – rectangular wave

DCR390J85



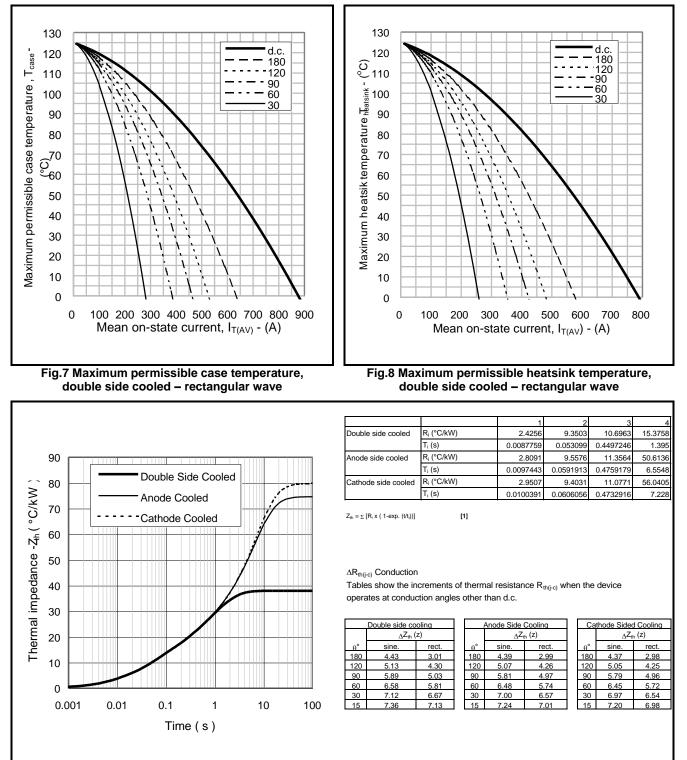
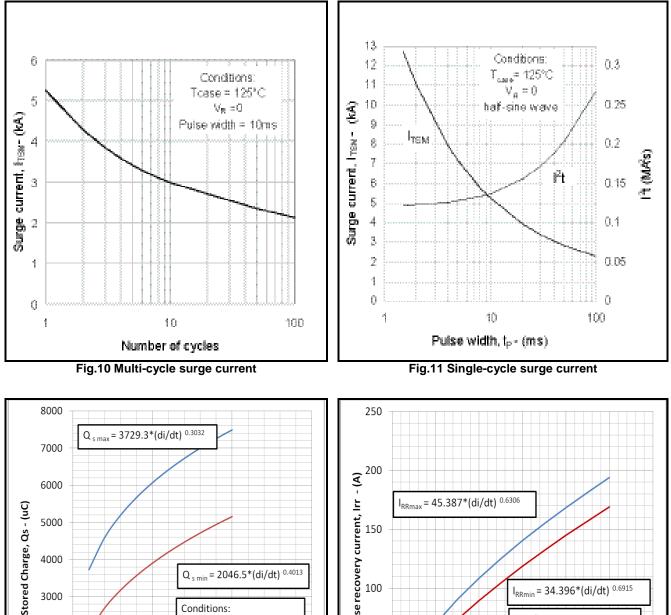


Fig.9 Maximum (limit) transient thermal impedance – junction to case (°C/kW)

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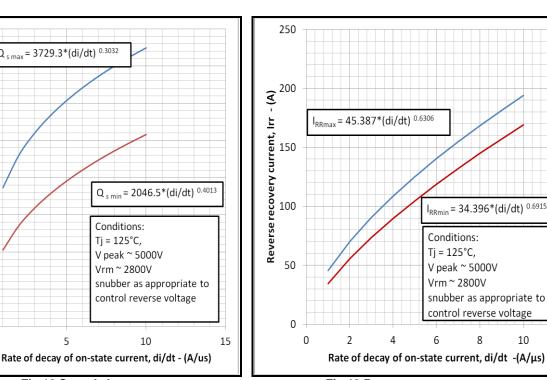


Fig.12 Stored charge

Fig.13 Reverse recovery current

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I_{RRmin} = 34.396*(di/dt) ^{0.6915}

snubber as appropriate to control reverse voltage

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Conditions:

Tj = 125°C,

V peak ~ 5000V

Vrm ~ 2800V

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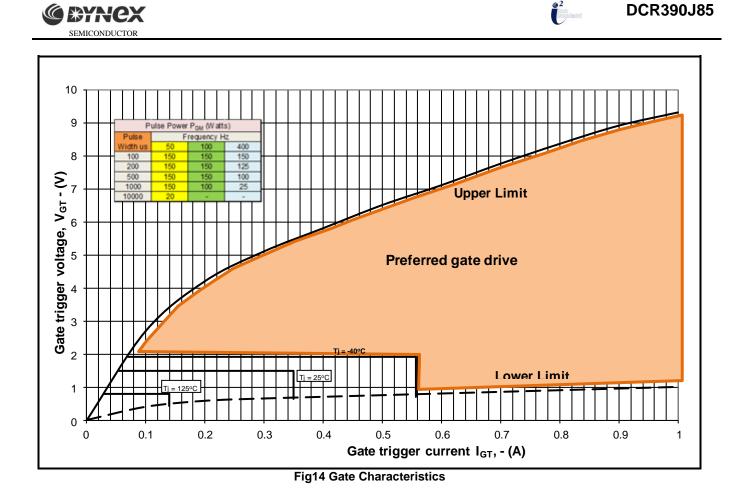
3000

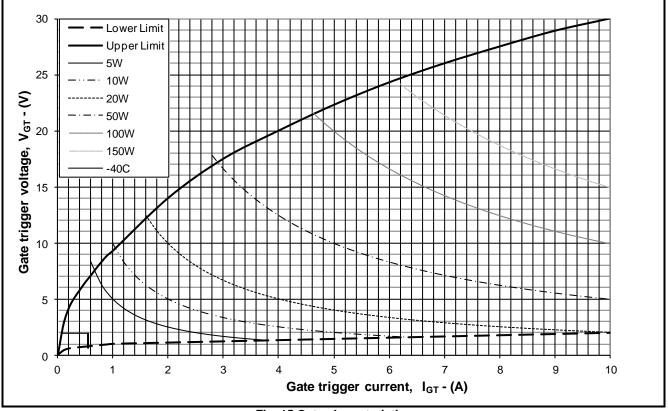
2000

1000

0

0







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PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

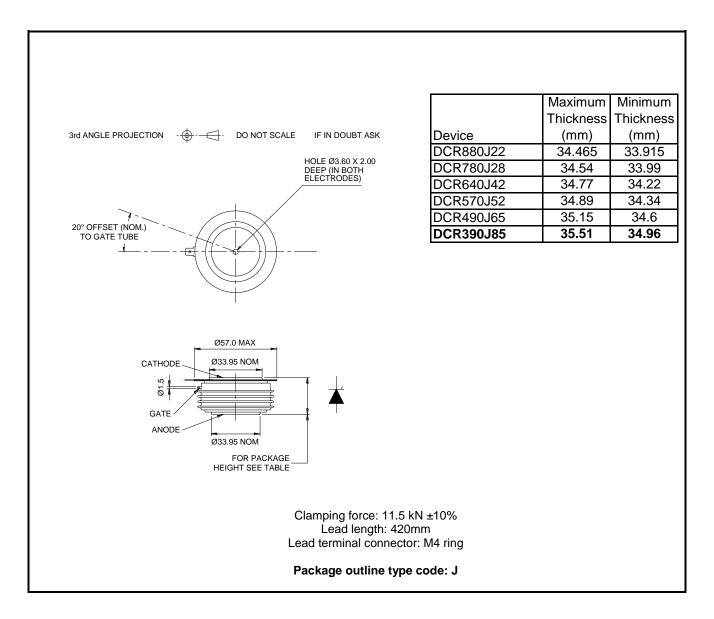


Fig.16 Package outline





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